

製品概要

NTHL020N120SC1: Silicon Carbide MOSFET, N-Channel, 1200 V, 20 mΩ , TO247-3L

技術情報は、データシートをご参照ください。

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

特長

- Max RDS(on) = 28mΩ at Vgs = 20V, Id = 60A
- High Speed Switching and Low Capacitance
- 1200V
- 100% UIL Tested

アプリケーション

- PFC
- Boost Inverter
- PV Charging

利点

- Typical RDS(on) = 20mΩ
- Coss = 260pF

最終製品

- Solar Inverter
- Network Power Supply
- Server Power Supply
- Charging Stations

電氣的仕様

製品	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	Blocking Voltage BV _{DSS} (V)	I _{D(max)} (A)	R _{DS(on)} Typ @ 25°C (mΩ)	Q _g Total (C)	Output Capacitance (C)	T _j Max (°C)	Package Type
NTHL020N120SC1	22.6408	Pb-free Halide free non AEC-Q and PPAP	Active	N-Channel	Single	1200	103	20	203	260	175	TO-247-3LD

詳細は、弊社 www.onsemi.jp の営業または販売代理店にお問い合わせください。

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